

MP02 XXX 175 Series

Phase Control Dual SCR, SCR/Diode Modules

Supersedes September 1992 version, 2.2

DS4477-3.0 December 1998

FEATURES

- Dual Device Module
- Electrically IsolatedPackage
- Pressure Contact Construction
- International Standard Footprint
- Alumina (non-toxic) Isolation Medium

APPLICATIONS

- Motor Control
- Controlled Rectifier Bridges
- Heater Control
- AC Phase Control

KEY PARAMETERS

 $\begin{array}{ll} \mathbf{V}_{\mathrm{DRM}} & \mathbf{1600V} \\ \mathbf{I}_{\mathrm{TSM}} & \mathbf{6800A} \\ \mathbf{I}_{\mathrm{T(AV)}} \text{ (per arm)} & \mathbf{175A} \\ \mathbf{V}_{\mathrm{isol}} & \mathbf{2500V} \end{array}$

CIRCUIT OPTIONS

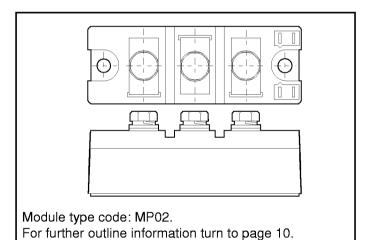
| Code | Circuit |
|------|---------|
| НВТ | |
| НВР | |
| HBN | |

VOLTAGE RATINGS

| Type Number | Repetitive Peak Voltages V _{DRM} V _{RRM} | Conditions |
|----------------|---------------------------------------------------------------------|---------------------------------------------------------------------------------|
| MP02/175-16 | 1600 | T _{vi} = 125°C |
| MP02/175-14 | 1400 | $I_{DRM} = I_{RRM} = 30 \text{mA}$ |
| MP02/175-12 | 1200 | $\begin{vmatrix} V_{DSM} & V_{RSM} = \\ V_{DRM} & V_{RRM} + 100V \end{vmatrix}$ |
| MP02/175-10 | 1000 | respectively |

Lower voltage grades available. 1800V product also available - consult factory. For full description of part number see "Ordering instructions" on page 3.

PACKAGE OUTLINE



CURRENT RATINGS - PER ARM

| Symbol | Parameter | Conditions | | Max. | Units |
|---------------------|-----------------------|----------------------------------------|------------------------------|------|-------|
| | Mean on-state current | | $T_{case} = 75^{\circ}C$ | 175 | Α |
| I _{T(AV)} | | | T _{case} = 85°C | 150 | Α |
| | | | T _{heatsink} = 75°C | 139 | Α |
| | | | T _{heatsink} = 85°C | 116 | Α |
| I _{T(RMS)} | RMS value | $T_{\text{case}} = 75^{\circ}\text{C}$ | | 275 | Α |

MP02 XXX 175 Series

SURGE RATINGS - PER ARM

| Symbol | Parameter | Conditions | | Max. | Units |
|------------------|-----------------------------------------|-------------------------------------------|---------------------------------------|--------|-------|
| I _{TSM} | Surge (non-repetitive) on-state current | 10ms half sine; T _j = 125°C | V _R = 0 | 6800 | Α |
| | | | V _R = 50% V _{RRM} | 5500 | Α |
| 124 | I ² t for fusing | 10ms half sine; T _j = 125°C | V _R = 0 | 231000 | A²s |
| l ² t | | | $V_{R} = 50\% V_{RRM}$ | 150000 | A²s |

THERMAL & MECHANICAL RATINGS

| Symbol | Parameter | Conditions | Max. | Units |
|-----------------------|--------------------------------------------------------------|------------------------------------------------------|------------|-------|
| | Thermal resistance - junction to case per Thyristor or Diode | dc | 0.19 | °C/W |
| $R_{th(j-c)}$ | | halfwave | 0.20 | °C/W |
| | | 3 phase | 0.21 | °C/W |
| R _{th(c-hs)} | Thermal resistance - case to heatsink per Thyristor or Diode | Mounting torque = 6Nm with mounting compound | 0.07 | °C/W |
| T _{vj} | Virtual junction temperature | | 125 | °C |
| T _{stg} | Storage temperature range | | -40 to 125 | °C |
| V _{isol} | Isolation voltage | Commoned terminals to base plate AC RMS, 1 min, 50Hz | 2.5 | kV |

DYNAMIC CHARACTERISTICS - THYRISTOR

| Symbol | Parameter | Conditions | Max. | Units | |
|-------------------------------------------------------------------------------|------------------------------------------|--------------------------------------------------------------------------------------------------|------|-------|--|
| V _{TM} | On-state voltage | At 1000A, T _{case} = 25°C | 1.75 | ٧ | |
| I _{RRM} /I _{DRM} | Peak reverse and off-state current | At V_{RRM}/V_{DRM} , $T_j = 125^{\circ}C$ | 30 | mA | |
| dV/dt | Linear rate of rise of off-state voltage | To 67% V _{DRM} , T _j = 125°C | 200* | V/µs | |
| dl/dt | Rate of rise of on-state current | From 67% V_{DRM} to 500A Gate source 10V, 5 Ω Rise time 0.5 μ s, T_j =125°C | 100 | A/μs | |
| V _{T(TO)} | Threshold voltage | At $T_{vj} = 125^{\circ}C$ | 1.05 | ٧ | |
| r _T | On-state slope resistance | At T _{vj} = 125°C | 0.80 | mΩ | |
| * Higher dV/dt values available, contact factory for particular requirements. | | | | | |

GATE TRIGGER CHARACTERISTICS AND RATINGS

| Symbol | Parameter | Conditions | | Max. | Units |
|------------------------|---------------------------|-------------------------------------------|---|------|-------|
| V _{GT} | Gate trigger voltage | $V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$ | - | 3.0 | ٧ |
| I _{GT} | Gate trigger current | $V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$ | - | 150 | mA |
| V _{GD} | Gate non-trigger voltage | $V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$ | - | 0.25 | ٧ |
| V _{FGM} | Peak forward gate voltage | Anode positive with respect to cathode | - | 30 | V |
| V _{FGN} | Peak forward gate voltage | Anode negative with respect to cathode | - | 0.25 | ٧ |
| V _{RGM} | Peak reverse gate voltage | | - | 5.0 | ٧ |
| I _{FGM} | Peak forward gate current | Anode positive with respect to cathode | - | 10 | Α |
| P _{GM} | Peak gate power | t _p = 25μs | - | 100 | W |
| P _{G(AV)} | Mean gate power | | ı | 5 | W |

ORDERING INSTRUCTIONS

Part number is made up as follows:

MP02 HBT 175 - 12

MP02 HBP175-12 MP02 HBN175-16 MP02 HBT175-10

Examples:

MP = Pressure contact module

02 = Outline type

HBT = Circuit configuration code (see "circuit options" - front page)

175 = Nominal average current rating at $T_{case} = 75^{\circ}C$

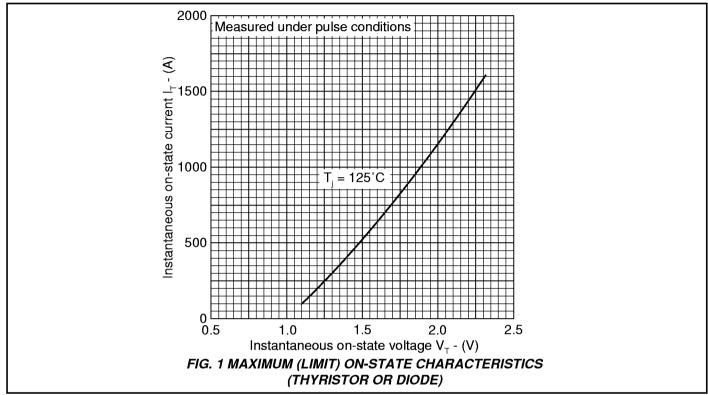
 $12 = V_{RRM}/100$

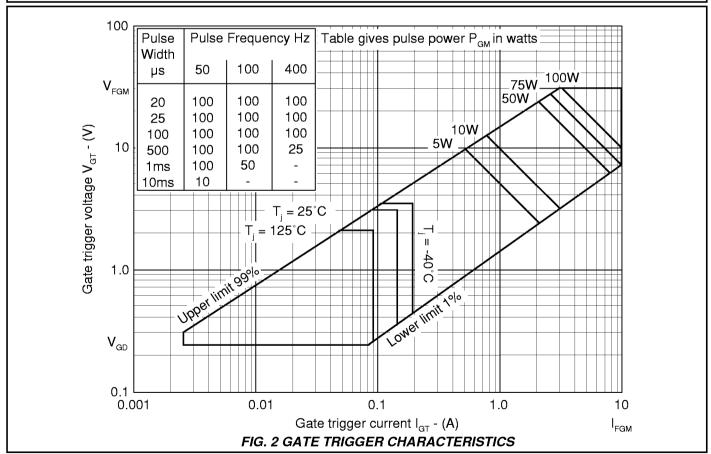
NOTE: Diode ratings and characteristics are comparable with the SCR in types HBP or HBN. Types HBP and HBN can also be supplied with diode polarity reversed, to special order.

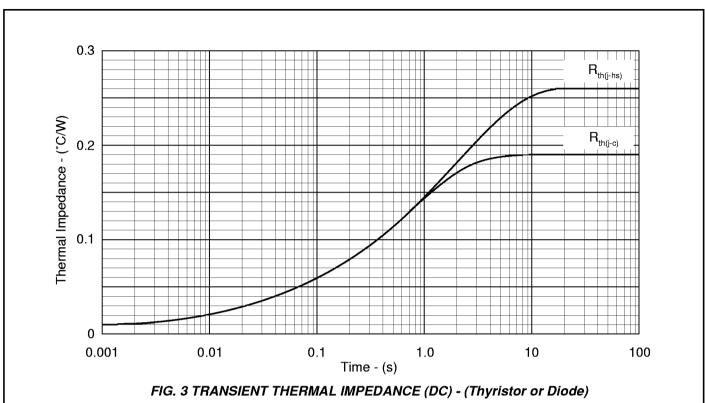
MOUNTING RECOMMENDATIONS

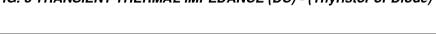
- Adequate heatsinking is required to maintain the base temperature at 75°C if full rated current is to be achieved. Power dissipation may be calculated by use of $V_{\text{T(TO)}}$ and r_{T} information in accordance with standard formulae. We can provide assistance with calculations or choice of heatsink if required.
- The heatsink surface must be smooth and flat; a surface finish of N6 (32 μ in) and a flatness within 0.05mm (0.002") are recommended.
- Immediately prior to mounting, the heatsink surface should be lightly scrubbed with fine emery, Scotch Brite or a mild chemical etchant and then cleaned with a solvent to remove oxide build up and foreign material. Care should be taken to ensure no foreign particles remain.
- An even coating of thermal compound (eg. Unial) should be applied to both the heatsink and module mounting surfaces. This should ideally be 0.05mm (0.002") per surface to ensure optimum thermal performance.
- After application of thermal compound, place the module squarely over the mounting holes, (or 'T' slots) in the heatsink. Using a torque wrench, slowly tighten the recommended fixing bolts at each end, rotating each in turn no more than 1/4 of a revolution at a time. Continue until the required torque of 6Nm (55lb.ins) is reached at both ends.
- It is not acceptable to fully tighten one fixing bolt before starting to tighten the others. Such action may DAMAGE the module.

CURVES









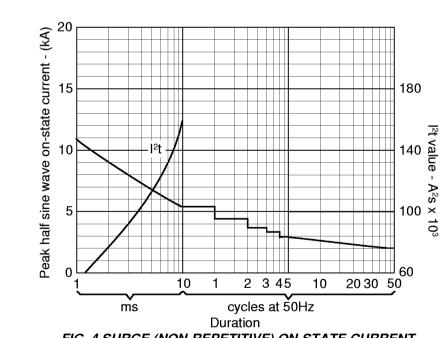


FIG. 4 SURGE (NON-REPETITIVE) ON-STATE CURRENT vs TIME (with 50% V_{RRM} T_{Case} 125°C) (Thyristor or Diode)

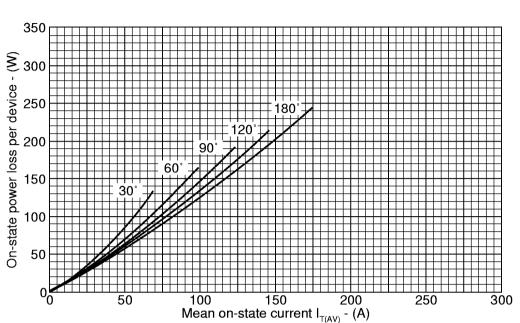


FIG. 5 ON-STATE POWER LOSS PER ARM vs FORWARD CURRENT AT VARIOUS CONDUCTION ANGLES, SINE WAVE, 50/60Hz.

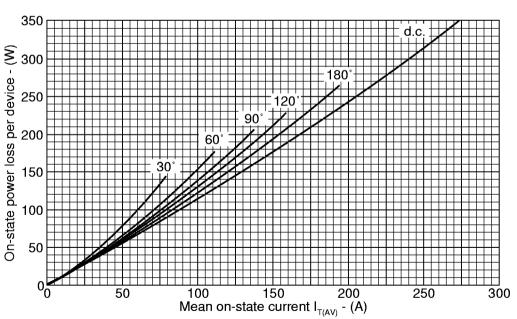
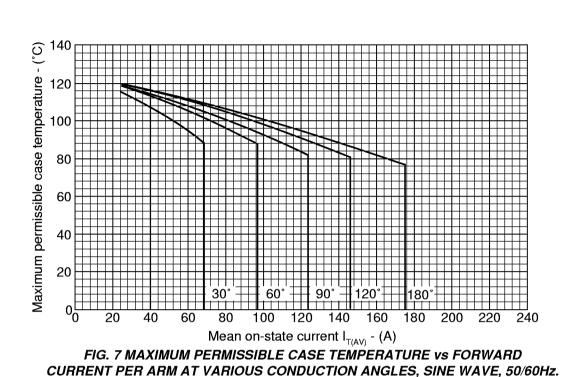
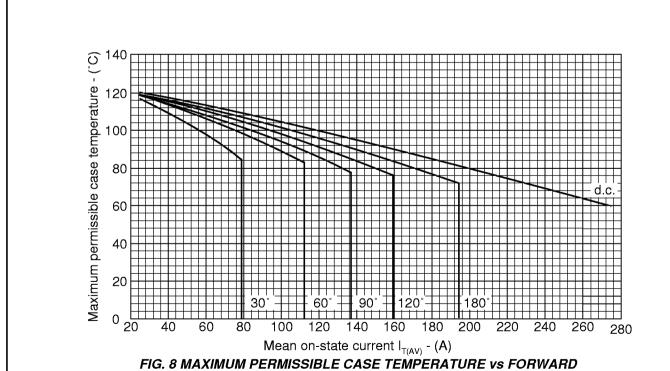


FIG. 6 ON-STATE POWER LOSS PER ARM VS FORWARD CURRENT AT VARIOUS CONDUCTION ANGLES, SQUARE WAVE, 50/60Hz.





CURRENT PER ARM AT VARIOUS CONDUCTION ANGLES, SQUARE WAVE, 50/60Hz.

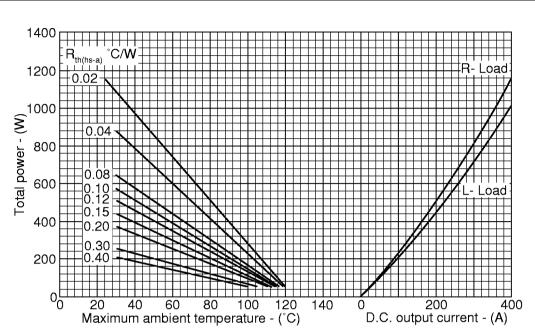


FIG. 9 50/60Hz SINGLE PHASE BRIDGE DC OUTPUT CURRENT VS POWER LOSS AND MAXIMUM PERMISSIBLE AMBIENT TEMPERATURE FOR VARIOUS VALUES OF HEATSINK THERMAL RESISTANCE.

(**Note:** $R_{th(hs-a)}$ values given above are **true** heatsink thermal resistances to ambient and already account for $R_{th(c-hs)}$ module contact thermal).

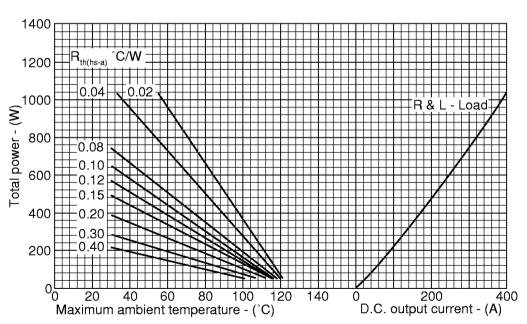
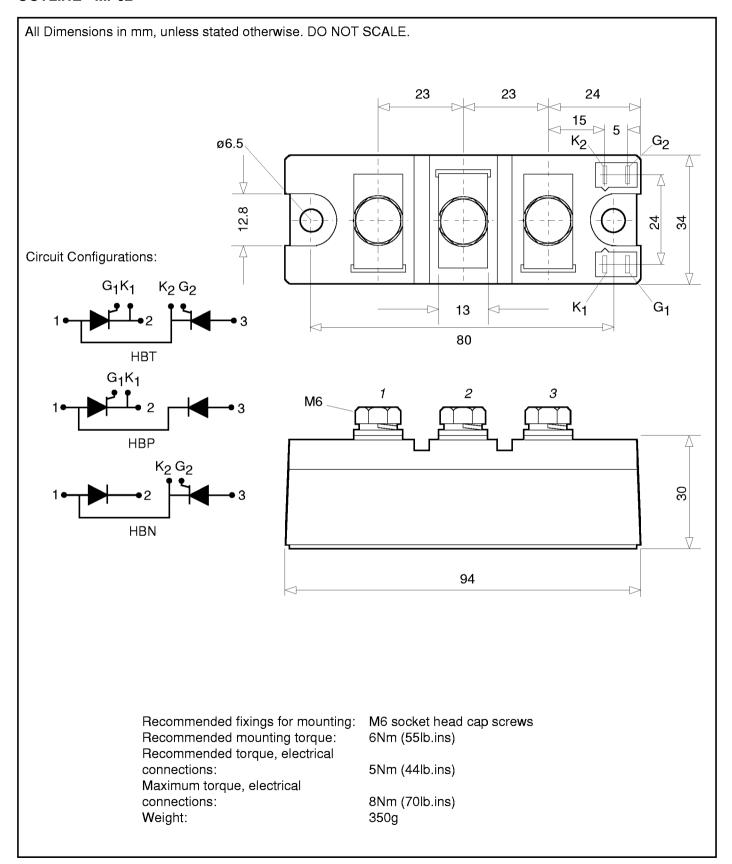


FIG. 10 50/60Hz 3-PHASE BRIDGE DC OUTPUT CURRENT vs POWER LOSS AND MAXIMUM PERMISSIBLE AMBIENT TEMPERATURE FOR VARIOUS VALUES OF HEATSINK THERMAL RESISTANCE.

(**Note:** $R_{th(hs-a)}$ values given above are **true** heatsink thermal resistances to ambient and already account for $R_{th(c-hs)}$ module contact thermal).

OUTLINE - MP02



MP02 XXX 175 Series



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